

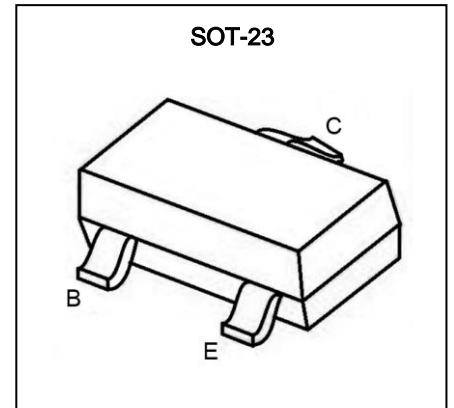
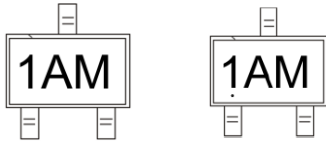


**MMBT3904 Transistor(NPN)**

**Feature**

- Switching Transistor
- Collector-emitter Voltage  $V_{CE}=40V$
- Collector Current  $I_C=0.2A$

**Marking**



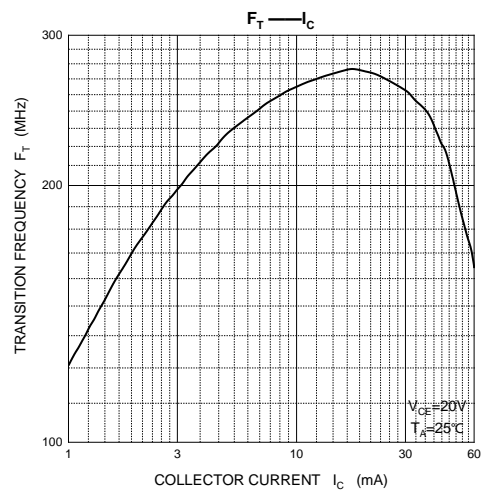
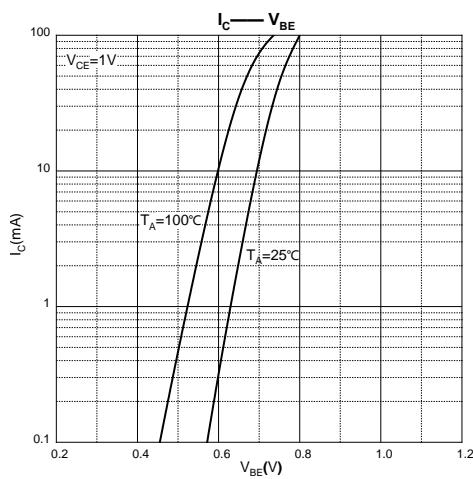
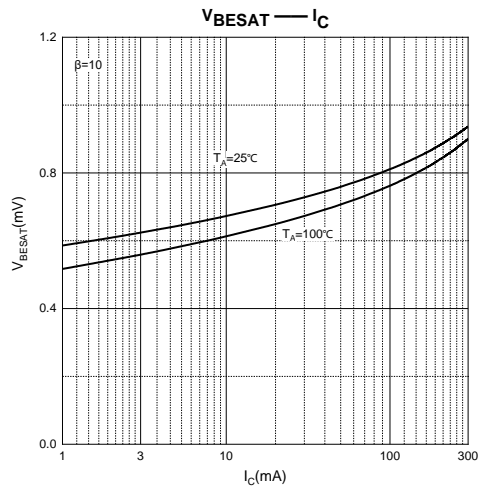
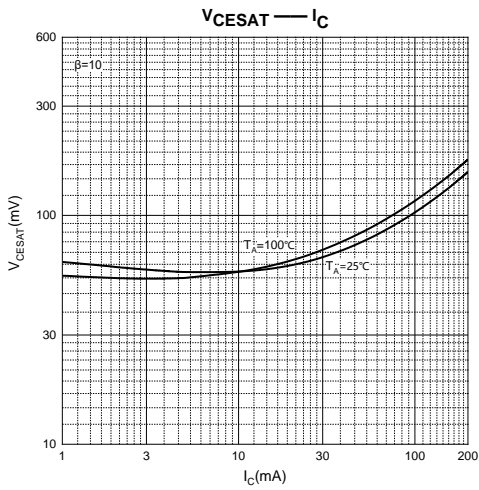
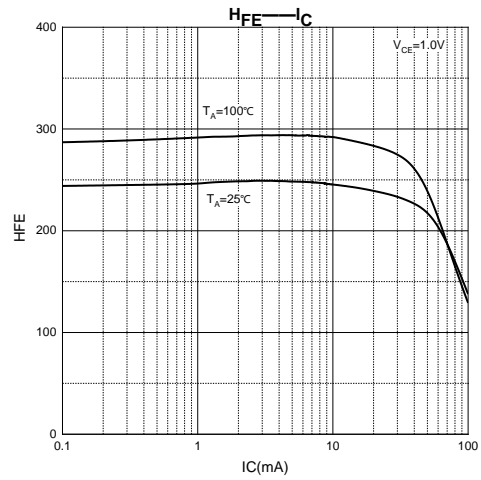
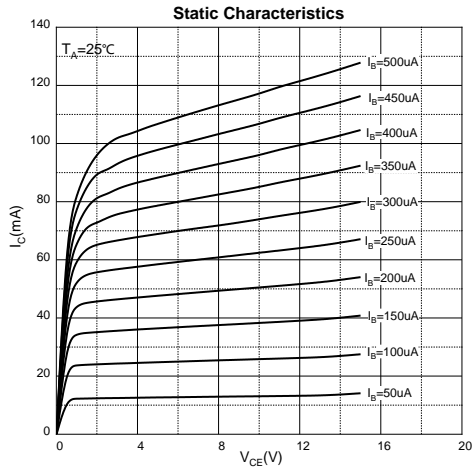
**MAXIMUM RATINGS ( $T_A=25^{\circ}C$  unless otherwise noted)**

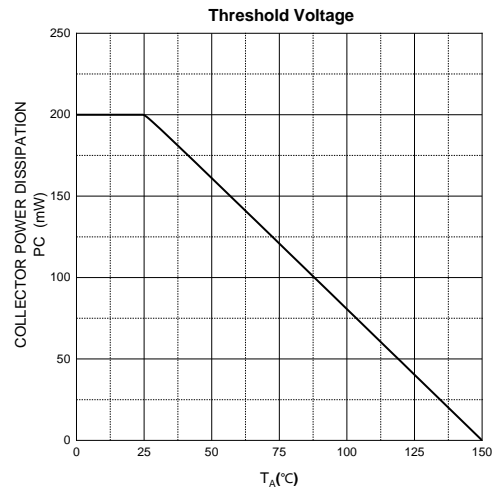
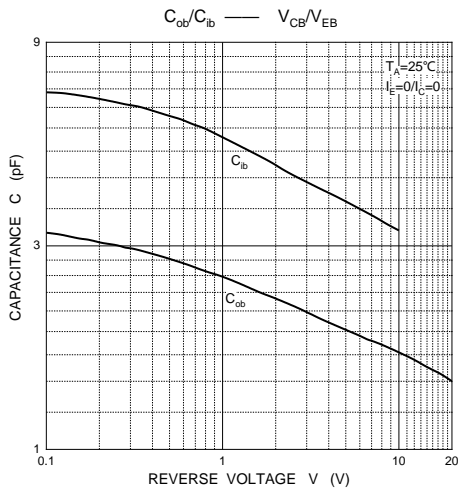
Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current -Continuous	$I_C$	0.2	A
Power Dissipation	$P_d$	0.35	W
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55~ +150	$^{\circ}C$

**ELECTRICAL CHARACTERISTICS(T<sub>A</sub>=25°C unless otherwise noted)**

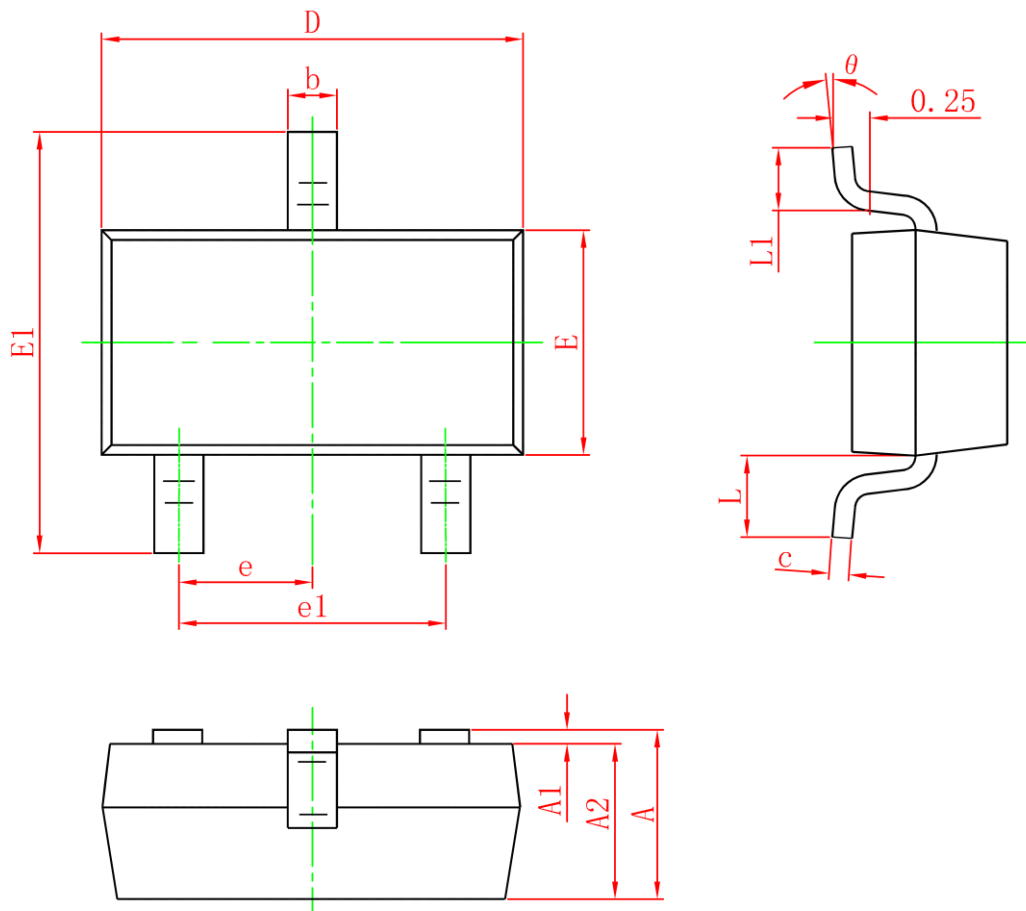
Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =10μA, I <sub>E</sub> =0	60		V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	40		V
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6		V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> =60V, I <sub>E</sub> =0		100	nA
Collector Cut-Off Current	I <sub>CEX</sub>	V <sub>CE</sub> =30V, V <sub>EB(off)</sub> =3V		50	nA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0		100	nA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =0.1mA	40		
	h <sub>FE2</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =1mA	70		
	h <sub>FE3</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =10mA	100	300	
	h <sub>FE4</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =50mA	60		
	h <sub>FE5</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =100mA	30		
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA		0.3	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA		0.95	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> =10mA, f=100MHz	300		MHZ
Delay Time	t <sub>d</sub>	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA,		35	ns
Rise Time	t <sub>r</sub>	V <sub>BE(off)</sub> =-0.5V, I <sub>B1</sub> =1mA		35	ns
Storage Time	t <sub>s</sub>	V <sub>CC</sub> =3V, I <sub>C</sub> =10mA,		200	ns
Fall Time	t <sub>f</sub>	I <sub>B1</sub> =I <sub>B2</sub> =1mA		50	ns

**Typical Characteristics**





## SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0	0.100	0	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.150	1.500	0.045	0.059
E1	2.250	2.650	0.089	0.104
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

**Attention:**

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.